

Technical Data Sheet Opto Interrupter SGM9302

Features

- Fast response time
- High analytic
- Peak wavelength λp=940nm
- High sensitivity
- Pb free



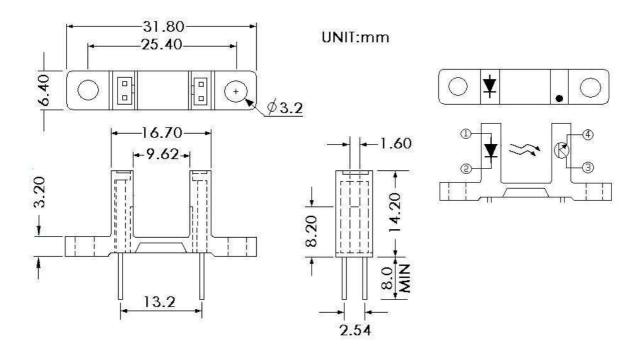
Descriptions

The SGM9302 consist of an infrared emitting diode and an NPN silicon phototransistor, encased side-by-side on converging optical axis in a black thermoplastic housing. The phototransistor receives radiation from the IR LED only. This is the normal situation. But when an object is in between, phototransistor could not receives the radiation.

Applications

- Non-contact Switching
- Switch Scanner
- For Direct Board
- Floppy disk driver

■ Package Dimensions



Notes:

- 1. All dimensions are in millimeters
- 2. Tolerances unless dimensions ±0.2mm
- 3. Lead spacing is measured where the lead emerge from the package

Absolute Maximum Ratings (Ta=25°℃)

Parameter		Symbol	Ratings	Unit
Input	Power Dissipation at(or below) 25°C Free Air Temperature	Pd	75	mW
	Reverse Voltage	V_R	5	V
	Forward Current	I_{F}	50	mA
	Peak Forward Current (*1) Pulse width $\leq 100 \mu$ s, Duty cycle=1%	${ m I_{FP}}$	1	A
Output	Collector Power Dissipation	Pd	75	mW
	Collector Current	I_{C}	20	mA
	Collector-Emitter Voltage	$\mathrm{B}\mathrm{V}_{\mathrm{CEO}}$	30	V
	Emitter-Collector Voltage	$\mathrm{B}\mathrm{V}_{\mathrm{ECO}}$	5	V
Operating Temperature		Topr	-25~+85	℃
Storage Temperature		Tstg	-40~+85	℃
Lead Soldering Temperature (*2) (1/16 inch form body for 5 seconds)		Tsol	260	$^{\circ}$ C

(*1) tw=100 μ sec. , T=10 msec. (*2) t=5 Sec SHENZHEN SHUGUAN ELECTRONIC TECHNOLOGY CO.,LTD. V1.0 2011.02.08



Electro-Optical Characteristics (Ta=25°C)

Parameter		Symbol	Min.	Тур.	Max.	Unit	Conditions	
Input	Forward Voltage	$V_{\rm F}$		1.2	1.5	V	$I_F=20mA$	
	Reverse Current	I_R			10	μ A	$V_R=5V$	
	Peak Wavelength	λp		940		nm	$I_F=20mA$	
	View Angle	201/2		60		Deg	I _F =20mA	
Output	Dark C urrent	I_{CEO}			100	nA	$V_{CE}=20V,Ee=0mW/cm^2$	
	C-E Saturation Voltage V _{CE} (sat	V (224)			0.4	V	$I_C=2mA$	
		V _{CE} (sat)					,Ee=1mW/cm ²	
Transfer Characteristics	Collect Current	I _C (ON)	0.5		10	mA	V _{CE} =5V	
		Ic(OFF)			20	μΑ	$I_F=20\text{mA}$	
	Rise time	$t_{\rm r}$		15		$\mu \sec$	V _{CE} =5V	
	Fall time	${ m t_f}$		15		$\mu \sec$	$I_{C}=1mA$	
							$R_L=1K\Omega$	

Typical Electrical/Optical/Characteristics Curves for IR

Fig.1 Forward Current vs.

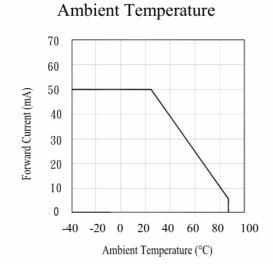


Fig.2 Spectral Distribution

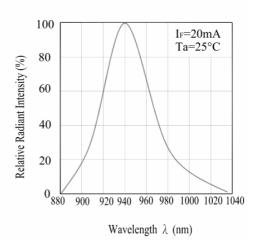


Fig.3 Peak Emission Wavelength vs. Ambient Temperature

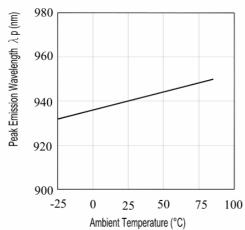


Fig.5 Forward Current vs

Ambient Temperature(°C)

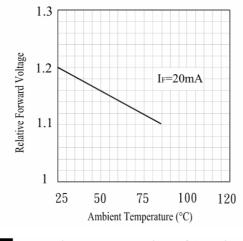


Fig.4 Forward Current

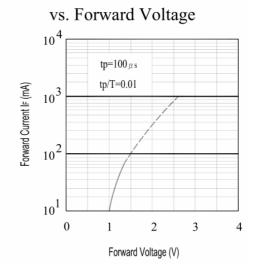
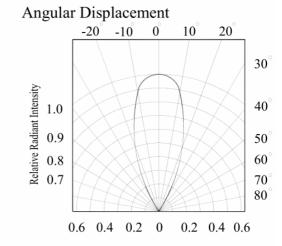


Fig.6 Relative Radiant Intensity vs.



Typical Electrical/Optical/Characteristics Curves for PT

Fig.1Collector Power Dissipation vs.

Ambient Temperature

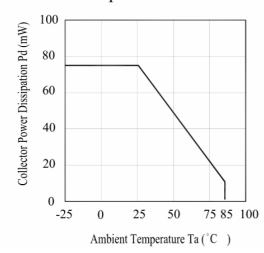


Fig.2 Spectral Sensitivity

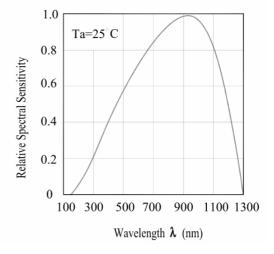


Fig.3 Relative Collector Current vs.



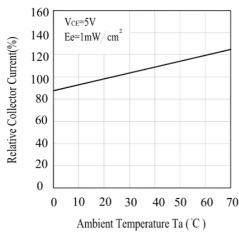


Fig.5 Collector Dark Current vs.

Ambient Temperature

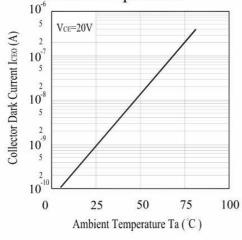


Fig.4 Collector Current vs.

Irradiance

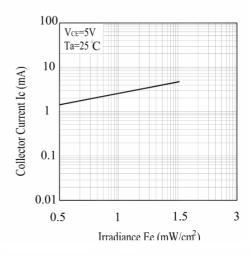
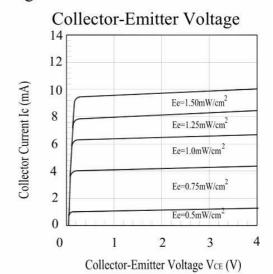


Fig.6 Collector Current vs.



■ Packing Quantity Specification

1. 100PCS/1Bag

■ Notes

- 1. Above specification may be changed without notice. SHUGUAN will reserve authority on material change for above specification.
- 2. When using this product, please observe the absolute maximum ratings and the instructions for using outlined in these specification sheets. SHUGUAN assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
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